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Editor

Fundamentals of Bias Temperature Instability in MOS Transistors

Characterization Methods,
Process and Materials Impact,
DC and AC Modeling

Contents

1	Introduction: Bias Temperature Instability (BTI)	
	in N and P Channel MOSFETs.	1
	Souvik Mahapatra, Nilesh Goel and Subhadeep Mukhopadhyay	
1.1	Introduction	1
1.2	Brief Overview of NBTI and PBTI	4
1.2.1	NBTI in SiO ₂ and SiON p-MOSFETs	5
1.2.2	NBTI and PBTI in HKMG MOSFETs	11
1.3	Ultra-Fast Characterization of NBTI in SiON p-MOSFETs	15
1.3.1	Process Impact on Threshold Voltage Degradation	16
1.3.2	Process Impact on NBTI Parameters	18
1.4	Ultra-Fast DC BTI Characterization in HKMG MOSFETs	22
1.4.1	Drain Current Degradation	23
1.4.2	Threshold Voltage Degradation	24
1.5	Ultra-Fast Characterization of BTI Recovery	
	and AC Degradation in HKMG MOSFETs	27
1.5.1	Recovery Measurements	27
1.5.2	AC BTI Measurements	29
1.6	Ultra-Fast Characterization of the Impact of HKMG EOT	
	Scaling on BTI	32
1.6.1	Effect of Nitrogen (N) Incorporation	32
1.6.2	Effect of Interlayer (IL) Scaling	35
1.7	Summary	36
	References	38

2 Characterization Methods for BTI Degradation and Associated Gate Insulator Defects	43
Souvik Mahapatra, Nilesh Goel, Ankush Chaudhary, Kaustubh Joshi and Subhadeep Mukhopadhyay	
2.1 Introduction	43
2.2 Ultra-Fast On-the-Fly (UF-OTF) Method	45
2.2.1 Impact of Measurement Delay for DC Stress	46
2.2.2 Recovery After DC Stress	49
2.3 Mobility Degradation	50
2.4 Ultra-Fast Measure-Stress-Measure (UF-MSM) Method	53
2.4.1 Measurements During DC Stress	54
2.4.2 Measurements During AC Stress	58
2.5 One Spot Drop Down (OSDD) Method	61
2.6 Flicker Noise	65
2.7 Charge Pumping (CP)	69
2.8 Gated Diode (DCIV)	75
2.9 Stress Induced Leakage Current (SILC)	78
2.10 Low Voltage Stress Induced Leakage Current (LV-SILC)	82
2.11 Experimental Artifacts	83
2.12 Summary	87
References	88
 3 Physical Mechanism of BTI Degradation—Direct Estimation of Trap Generation and Trapping	 93
Subhadeep Mukhopadhyay and Souvik Mahapatra	
3.1 Introduction	93
3.2 Description of HKMG Devices	96
3.3 Trap Generation During NBTI	97
3.3.1 DCIV Measurements in DC Stress	98
3.3.2 DCIV Measurements in AC Stress	101
3.4 Hole Trapping During NBTI	103
3.5 Trap Generation During PBTI	106
3.5.1 DCIV Measurements in DC Stress	107
3.5.2 DCIV Measurements in AC Stress	110
3.5.3 SILC Measurements in DC Stress	111
3.6 Electron Trapping During PBTI	115
3.7 Location of Generated Traps (DCIV Measurements)	118
3.8 Summary	121
References	122

4	Physical Mechanism of BTI Degradation—Modeling of Process and Material Dependence	127
	Souvik Mahapatra, Kaustubh Joshi, Subhadeep Mukhopadhyay, Ankush Chaudhary and Nilesh Goel	
4.1	Introduction	127
4.2	Compact Model and Device Description	130
4.2.1	NBTI Model	130
4.2.2	PBTI Model.	132
4.2.3	Process Dependence	134
4.3	NBTI Process Dependence in SiON p-MOSFETs	136
4.4	NBTI Process Dependence in HKMG p-MOSFETs	141
4.4.1	Impact of HKMG Process	141
4.4.2	Impact of Channel Material	148
4.4.3	Impact of Channel Orientation (FinFETs)	153
4.5	Process Impact on NBTI Parameters	156
4.5.1	Time Exponent.	156
4.5.2	Temperature Activation	161
4.5.3	Field Acceleration.	164
4.6	PBTI Process Dependence in HKMG n-MOSFETs	167
4.7	Summary.	174
	References	175
5	Reaction-Diffusion Model	181
	Ahmad Ehteshamul Islam, Nilesh Goel, Souvik Mahapatra and Muhammad Ashraful Alam	
5.1	Introduction	182
5.2	RD Formalism for the NBTI Stress Phase	183
5.2.1	Diffusing/Drifting Species in RD Formalism	185
5.2.2	Features of RD Formalism for NBTI Stress Phase	191
5.3	RD Formalism for NBTI Relaxation Phase	192
5.4	RD Formalism for AC NBTI Stress	195
5.4.1	Frequency Independence	197
5.4.2	Duty Cycle Dependence	197
5.5	Key Features of RD Theory.	198
5.6	Mechanism of Si–H Bond Dissociation.	199
5.6.1	Hole-Assisted, Field-Enhanced, Thermal Dissociation of Si–H Bond	199
5.6.2	Theoretical Estimation of Tunneling Factors.	201
5.6.3	Theoretical Estimation of Effective Dipole Moment	202
5.6.4	Procedure for Estimating Model Parameters	202
5.7	Summary.	204
	References	204

6 Modeling of DC and AC NBTI Degradation and Recovery for SiON and HKMG MOSFETs 209
Nilesh Goel and Souvik Mahapatra 209
6.1 Introduction 209
6.2 Degradation During DC Stress 213
6.2.1 Reaction-Diffusion (RD) Model for Interface Trap Generation 215
6.2.2 Experimental Validation of RD Model 219
6.2.3 Hole Trapping and Bulk Trap Generation 221
6.2.4 SiON Process Dependence 222
6.2.5 HKMG Process Dependence 224
6.3 Recovery After DC Stress 227
6.3.1 Modeling Framework 228
6.3.2 Analysis of SiON and HKMG Devices 232
6.4 Degradation During AC Stress 236
6.4.1 RD Model for Generation of Interface Traps 237
6.4.2 Transient Trap Occupancy Calculation 239
6.4.3 Hole Trapping and Detrapping 243
6.4.4 Analysis of Experimental Results 243
6.4.5 Comparative Analysis of Mode-A and Mode-B Stress 249
6.5 Compact Model for DC and AC Degradation 252
6.6 Summary 256
References 258

Index 265